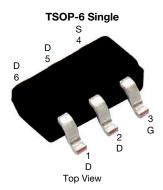




N-Channel 100 V (D-S) MOSFET

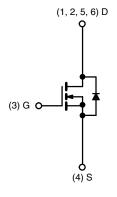


PRODUCT SUMMARY						
V _{DS} (V)	100					
$R_{DS(on)}$ max. (Ω) at V_{GS} = 10 V	0.170					
$R_{DS(on)}$ max. (Ω) at $V_{GS} = 6 \text{ V}$	0.185					
Q _g typ. (nC)	5.5					
I _D (A)	2.4					
Configuration	Single					

FEATURES

- High-efficiency PWM optimized
- 100 % R_g tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





N-Channel MOSFET

ORDERING INFORMATION				
Package	TSOP-6			
Lead (Pb)-free	Si3430DV-T1-E3			
Lead (Pb)-free and halogen-free	Si3430DV-T1-GE3			

ABSOLUTE MAXIMUM RATINGS (TA	= 25 °C, unless	s otherwise n	oted)			
PARAMETER		SYMBOL	5 s	STEADY STATE	UNIT	
Drain-source voltage	V _{DS}	100	100	V		
Gate-source voltage	V_{GS}	± 20	± 20	V		
Continuous drain current (T _J = 175 °C) ^a	T _A = 25 °C		2.4	1.8	A	
	T _A = 85 °C	l _D	1.7	1.3		
Pulsed drain current	I _{DM}	8	8	A		
Avalanche current	L = 0.1 mH	I _{AR}	6	6		
Repetitive avalanche energy (duty cycle ≤ 1 %)	L = 0.1 IIII	E _{AR}	1.8	1.8	mJ	
Continuous source current (diode conduction) ^a		I _S	1.7	1	Α	
Maximum power discipation 8	T _A = 25 °C	В	2	1.14	W	
Maximum power dissipation ^a	T _A = 85 °C	P _D	1	0.59	VV	
Operating junction and storage temperature range		T _J , T _{sta}	-55 to +150	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum junction-to-ambient ^a	t ≤ 5 s	R _{thJA}	45	62.5	°C/W
	Steady state		90	110	
Maximum junction-to-foot (drain)	Steady state	Rt _{hJF}	25	30	

Note

a. Surface mounted on 1" x 1" FR4 board



www.vishay.com

Vishay Siliconix

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						
Gate threshold voltage	V _{GS(th)}	$V_{DS} = V_{DS}$, $I_D = 250 \mu A$	2	-	4.2	V
Gate-body leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zero gate voltage drain current	1	$V_{DS} = 80 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1	μΑ
Zero gate voltage drain current	I _{DSS}	V_{DS} = 80 V, V_{GS} = 0 V, T_J = 85 °C	-	-	25	
On-state drain current a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	8	-	-	Α
Drain-source on-state resistance a	В	$V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$	-	0.148	0.170	Ω
Drain-source on-state resistance "	R _{DS(on)}	$V_{GS} = 6 \text{ V}, I_D = 2.3 \text{ A}$	-	0.160	0.185	
Forward transconductance a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 2.4 \text{ A}$	-	7	-	S
Diode forward voltage a	V _{SD}	I _S = 1.7 A, V _{GS} = 0 V	-	0.8	1.2	V
Dynamic ^b						
Total gate charge	Q_{g}		-	5.5	8.2	
Gate-source charge	Q_{gs}	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.4 \text{ A}$	-	1.5	-	nC
Gate-drain charge	Q_{gd}		-	1.4	-	
Gate resistance	R_g		1	-	4	Ω
Turn-on delay time	t _{d(on)}		-	9	20	
Rise time	t _r	$V_{DD} = 50 \text{ V}, R_1 = 50 \Omega$	-	11	20	no
Turn-off delay time	t _{d(off)}	$I_D\cong 1$ A, $V_{GEN}=10$ V, $R_g=6$ Ω	-	16	30	ns
Fall time	t _f		-	9	20	
Gate resistance	Rg	V _{GS} = 0.1 V, f = 5 MHz	-	2.8	-	Ω
Source-drain reverse recovery time	t _{rr}	I _F = 1.7 A, di/dt = 100 A/μs	-	50	80	ns

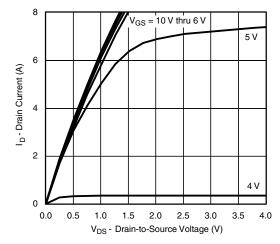
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing

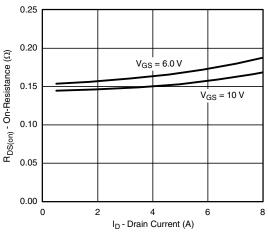
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



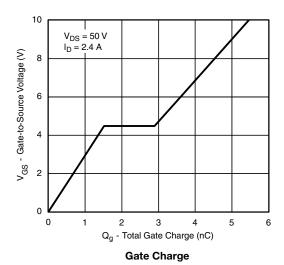
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

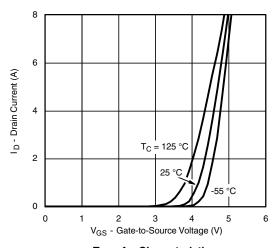


Output Characteristics

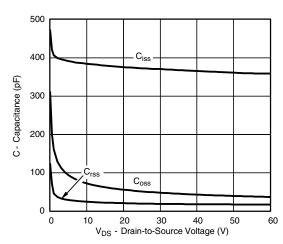


On-Resistance vs. Drain Current

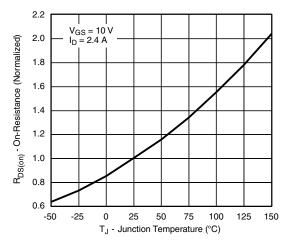




Transfer Characteristics



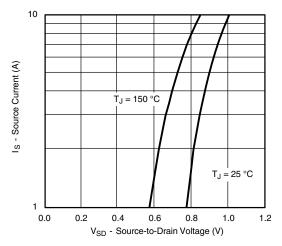
Capacitance



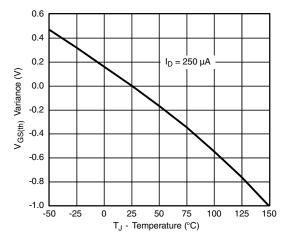
On-Resistance vs. Junction Temperature



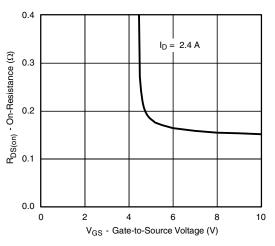
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



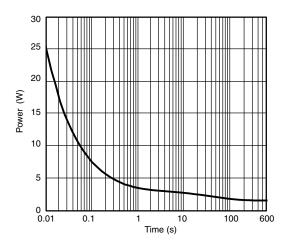
Source-Drain Diode Forward Voltage



Threshold Voltage



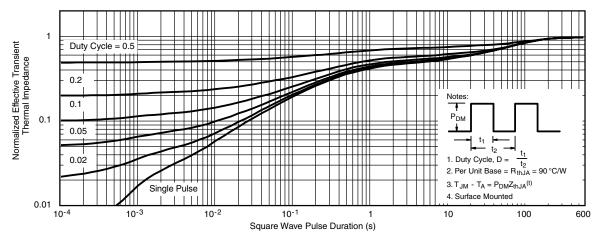
On-Resistance vs. Gate-to-Source Voltage



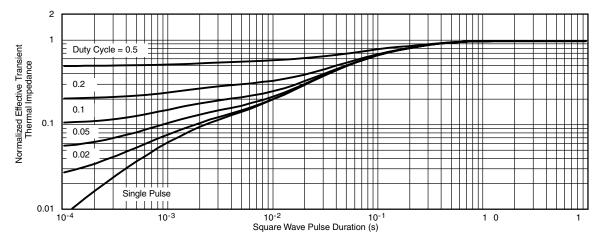
Single Pulse Power



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

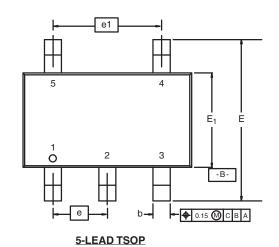
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?71235.

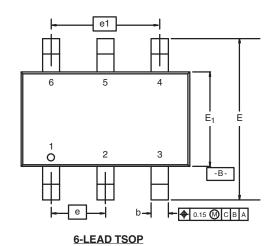


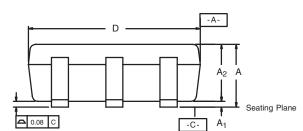


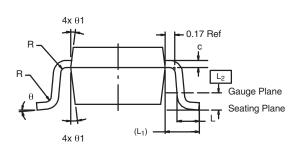
TSOP: 5/6-LEAD

JEDEC Part Number: MO-193C









	MIL	LIMETER	RS	INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012 0.013		0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
E	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е		0.95 BSC		0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.079		
L	0.32	-	0.50	0.012	-	0.020	
L ₁	0.60 Ref				0.024 Ref		
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ_1		7° Nom			7° Nom		
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							

Document Number: 71200 www.vishay.com 18-Dec-06



Recommended Land Pattern For TSOP-5L / TSOP-6L



Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022 DWG: 3010



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.